

# GaAs IC High Isolation Positive Control SPDT Switch DC–2.5 GHz



AS118-12

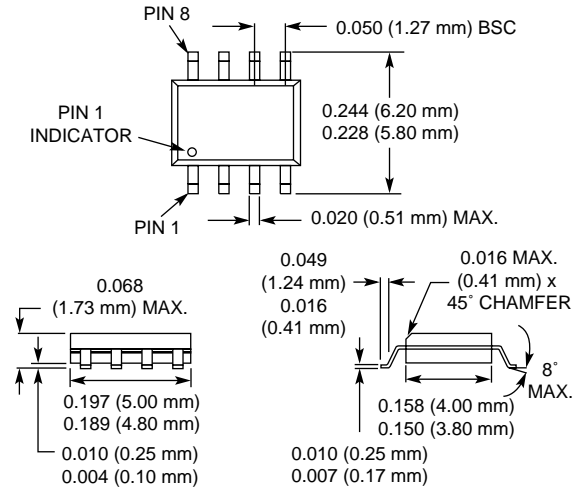
## Features

- Positive Control
- High Isolation (45 dB @ 0.9 GHz)
- Low Insertion Loss (0.5 dB @ 0.9 GHz)

## Description

The AS118-12 is a reflective SPDT FET IC switch. The switch requires external DC blocking capacitors, positive supply and two positive controls. The device is mounted in a plastic SOIC-8 package for surface mounting and is ideal for use in high isolation switching applications, such as base station synthesizer switching.

## SOIC-8



## Electrical Specifications at 25°C (0, +5 V)

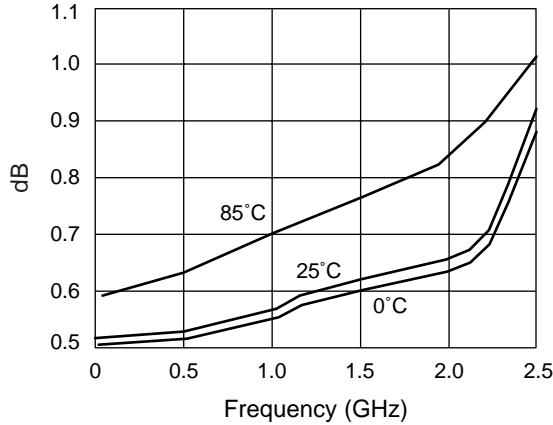
Parameter <sup>1</sup>	Frequency <sup>2</sup>	Min.	Typ.	Max.	Unit
Insertion Loss <sup>3</sup>	DC–0.5 GHz		0.55	0.65	dB
	DC–1.0 GHz		0.6	0.7	dB
	DC–2.0 GHz		0.7	0.8	dB
	DC–2.5 GHz		0.9	1.1	dB
Isolation	DC–0.5 GHz	46	50		dB
	DC–1.0 GHz	43	46		dB
	DC–2.0 GHz	24	27		dB
	DC–2.5 GHz	15	18		dB
VSWR <sup>4</sup>	DC–1.0 GHz		1.2:1	1.4:1	
	DC–2.0 GHz		1.4:1	1.7:1	
	DC–2.5 GHz		1.6:1	2.1:1	

## Operating Characteristics at 25°C (0, +5 V)

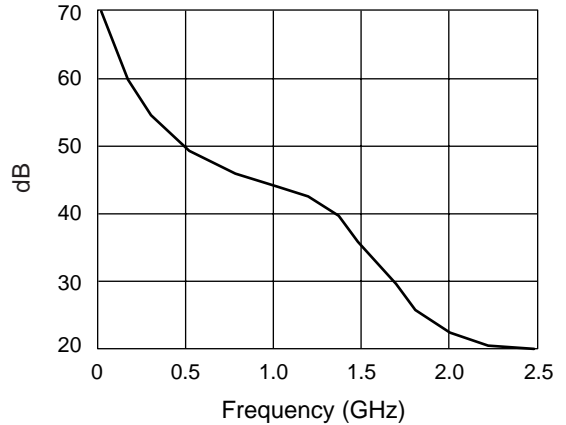
Parameter <sup>1</sup>	Condition	Frequency	Min.	Typ.	Max.	Unit
Switching Characteristics <sup>5</sup>	Rise, Fall (10/90% or 90/10% RF)			60		ns
	On, Off (50% CTL to 90/10% RF)			100		ns
	Video Feedthru			50		mV
Input Power for 1 dB Compression		0.9 GHz		+26		dBm
Intermodulation Intercept Point (IP3)	For Two-tone Input Power +10 dBm	0.9 GHz		+41		dBm
Control Voltages	$V_{Low} = 0 \text{ to } 0.2 \text{ V @ } 20 \mu\text{A Max.}$ $V_{High} = +3 \text{ V @ } 100 \mu\text{A Max. to } +5 \text{ V @ } 200 \mu\text{A Max.}$ $V_S = V_{High} \pm 0.2 \text{ V}$					

1. All measurements made in a 50 Ω system, unless otherwise specified.
2. DC = 300 kHz.
3. Insertion loss changes by 0.003 dB/°C.
4. Insertion loss state.
5. Video feedthru measured with 1 ns risetime pulse and 500 MHz bandwidth.

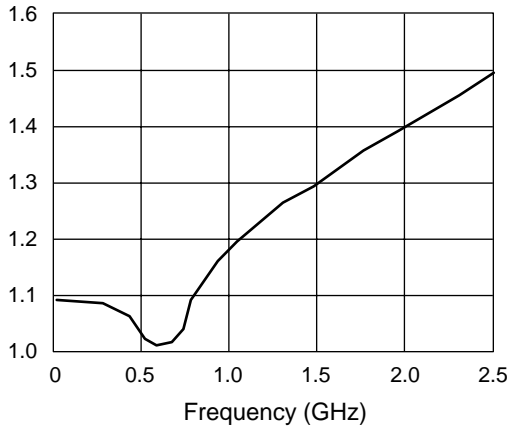
**Typical Performance Data (0, +5 V)**



**Insertion Loss vs. Frequency**



**Isolation vs. Frequency**



**VSWR vs. Frequency**

**Truth Table**

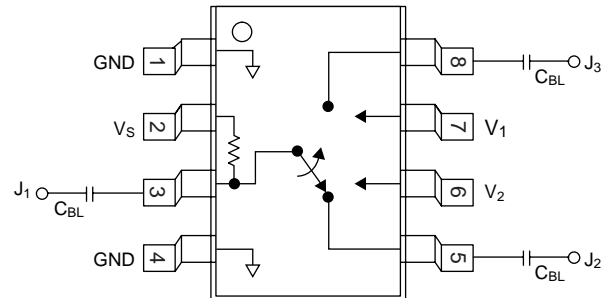
V <sub>1</sub>	V <sub>2</sub>	J <sub>1</sub> -J <sub>2</sub>	J <sub>1</sub> -J <sub>3</sub>
V <sub>High</sub>	0	Insertion Loss	Isolation
0	V <sub>High</sub>	Isolation	Insertion Loss

V<sub>High</sub> = +3 to +5 V (V<sub>S</sub> = V<sub>High</sub> ± 0.2 V).

**Absolute Maximum Ratings**

Characteristic	Value
RF Input Power	1 W Max. > 0.9 GHz 0/+5 V Control
Supply Voltage	+8 V
Control Voltage	-0.2 V, +8 V
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C
Θ <sub>JC</sub>	85°C/W

**Pin Out**



DC blocking capacitors (C<sub>BL</sub>) must be supplied externally.  
C<sub>BL</sub> = 100 pF for operation >500 MHz.